

LISTING OF THE CLAIMS

Please amend claims 9-10, and cancel claims 1-5, 7-8 and 11-18 as indicated below. This listing of claims replaces all prior versions.

1. (Cancelled)

2. (Cancelled)

3. (Cancelled)

4. (Cancelled)

5. (Cancelled)

6. (Cancelled)

7. (Cancelled).

8. (Cancelled)

9. (Currently Amended) A semiconductor device as claimed in claim 1, including a semiconductor region having p and n semiconductor regions which form a pn junction and a field shaping region located adjacent only one of the p and n semiconductor regions to increase the reverse breakdown voltage of the device, wherein the field shaping region is insulating material and the field shaping region extends from a first capacitive voltage coupling region to a second capacitive voltage coupling region which are provided to apply, in use, substantially the same voltages as are applied to the pn junction, the material and capacitive coupling of the field shaping region being such that, when a reverse voltage is applied across the pn junction and the device is non-conducting, a capacitive electric field is present in a part of the field shaping region which extends beyond a limit of the pn junction depletion region which would exist in the absence of the

field shaping region, the electric field in the field shaping region inducing a stretched electric field limited to a correspondingly stretched pn junction depletion region in the semiconductor region, wherein at least one of the first and second capacitive voltage coupling regions comprises one of the p and n semiconductor regions which form the pn junction.

10. (Currently Amended) A semiconductor device as claimed in claim 1, including a semiconductor region having p and n semiconductor regions which form a pn junction and a field shaping region located adjacent only one of the p and n semiconductor regions to increase the reverse breakdown voltage of the device, wherein the field shaping region is insulating material and the field shaping region extends from a first capacitive voltage coupling region to a second capacitive voltage coupling region which are provided to apply, in use, substantially the same voltages as are applied to the pn junction, the material and capacitive coupling of the field shaping region being such that, when a reverse voltage is applied across the pn junction and the device is non-conducting, a capacitive electric field is present in a part of the field shaping region which extends beyond a limit of the pn junction depletion region which would exist in the absence of the field shaping region, the electric field in the field shaping region inducing a stretched electric field limited to a correspondingly stretched pn junction depletion region in the semiconductor region, wherein at least one of the first and second capacitive voltage coupling regions comprises a more highly doped semiconductor region of the same conductivity type and adjacent one of the p and n semiconductor regions which form the pn junction.

11. (Cancelled)

12. (Cancelled)

13. (Cancelled)

14. (Cancelled)

15. (Cancelled)

16. (Cancelled)

17. (Cancelled)

18. (Cancelled)